

# General Viva-voce ~~ex~~ questions

1. LASER Acronym  $\Rightarrow$  ~~Laser~~ A  
Light Amplification by Stimulated Emission  
of Radiation
2. Properties (or) characteristics of Laser over ordinary light
  - i) monochromatic ii) coherent
  - iii) High directionality iv) High Intensity
- 3) Diode?  $\Rightarrow$  It is a device consists of  
2 electrodes namely anode & cathode
- 4) Input and output of <sup>8LED</sup> LASER Diode  $\Rightarrow$   
Electrical energy into Light Energy
- 5) Diffraction  $\Rightarrow$  bending of light beams
- 6) Grating  $\Rightarrow$  glass material ~~is~~ consists of  
number of vertical straight lines  
[ 2500 lines/inch; 98425 lines/m ]
- 7) Optical fiber? cylindrical dielectric light  
guiding medium
- 8) Principle of optical fiber: Total Internal  
Reflection

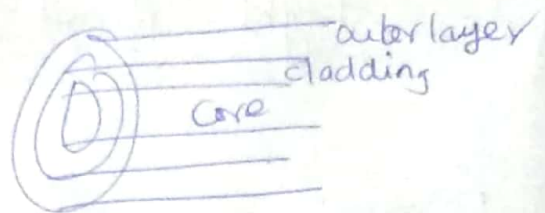
## Two conditions

- i)  $n_1 > n_2$
- ii)  $\theta_i > \theta_c$

$n_1$  - refractive index of Core

$n_2$  - " of cladding

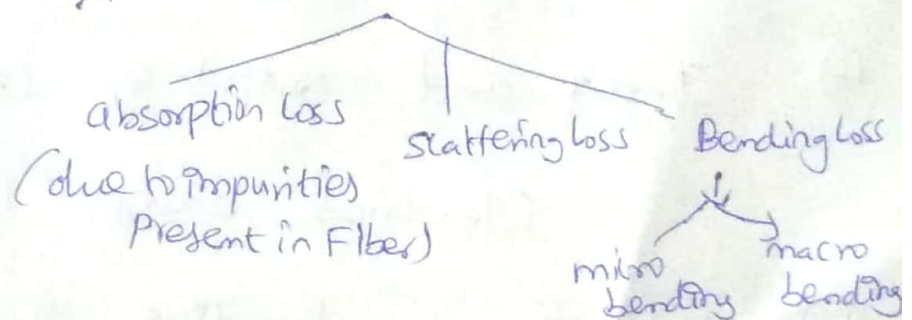
## 9) Construction of OF



## 10) The light sources for OF: i) LASER ii) LED

11) ~~Loss~~ + Numerical aperture: light gathering ability of OF cable

12) Loss in OF: Light signal loss in amplitude is called attenuation



13) Energy band gap is called as energy difference between conduction band and valence band

$$E_g = E_c - E_v \quad E_g = \frac{hc}{\lambda} \text{ eV}$$

14) Principle of LASER  $\Rightarrow$  Stimulated emission (read def)  
Principle of LED  $\Rightarrow$  Electroluminescence

15) Difference b/w normal p-n junction diode and LED, LASER Diode

normal diode is made up of Indirect band gap  
LED, LASER is made up of Direct band gap ex: mas semiconductors Ex: Ga, Si

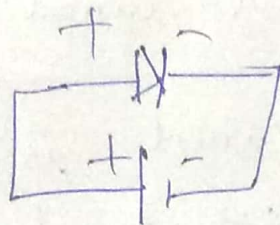


16) LED different colours - By varying the impurity concentration and selecting the material

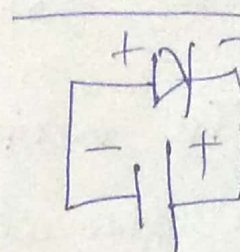
17) LED - Converting Electrical energy into optical energy

18) LED & LASER Diode  $\Rightarrow$  working under forward biased condition

Forward Bias



Reverse bias



19) threshold voltage: The voltage at which the diode starts to conduct the electricity or remove the potential barrier in p-n junction  
or knee voltage

20)  $E_g$  of Si = 1.1 eV ;  $E_g$  of Ge = 0.7 eV

21) photodiode  $\Rightarrow$  converts Light energy into electrical energy under reverse biased p-n junction

22) Total current in the photodiode = dark current +

$$I_T = I_d + I_p$$

(without light)      (with light)

[  $\frac{A}{\text{optical}}$  photocurrent communication system ]

23) Solar cell  $\Rightarrow$  converts ~~Electrical~~ Light energy into electrical energy  
 $\Rightarrow$  operating in ~~photoconductor~~ photovoltaic mode



24) Indirect band gap semiconductors are used to fabricate the solar cell.

25) Open circuit voltage ( $V_{oc}$ ) :

The maximum voltage is delivered by the solar cell with load resistance ( $R_L$ )

II Short circuit current density ( $I_{sc}$ )

The maximum current is delivered by the solar cell without load resistance ( $R_L$ )

26) Fill Factor : measure the quality of the Solar cell

Prepare more questions from Lab manual also

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